PBSS4021NX

20 V, 7 A NPN low VCEsat (BISS) transistor

11 December 2012

Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS4021PX.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	7	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	15	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	19	28	mΩ



20 V, 7 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		2
2	С	collector		3——
3	В	base	3 2 1 SOT89	1 sym042

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS4021NX	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
PBSS4021NX	%6D

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

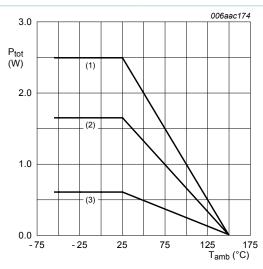
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	7	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	15	Α
I _B	base current			-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	600	mW
			[2]	-	1650	mW
			[3]	-	2500	mW
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Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	150	°C
T _{stg}	storage temperature		-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ang a)	thermal resistance	in free air	[1]	-	-	210	K/W
	from junction to ambient		[2]	-	-	75	K/W
	ambient		[3]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

PBSS4021NX

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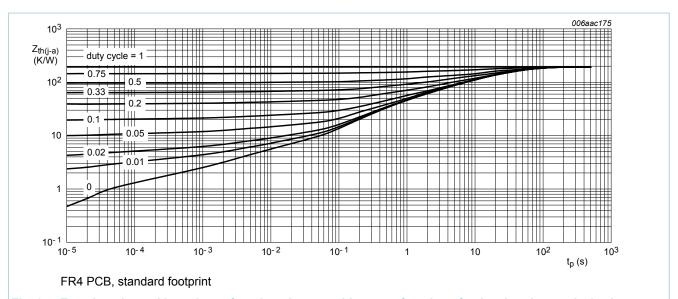


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

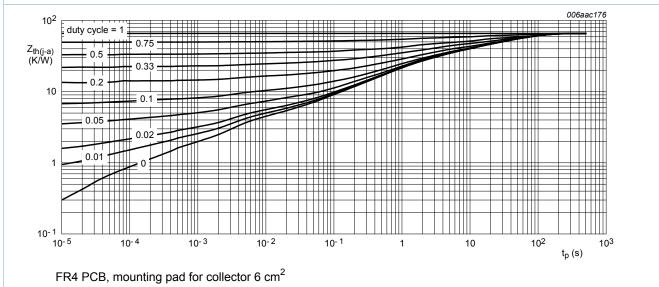
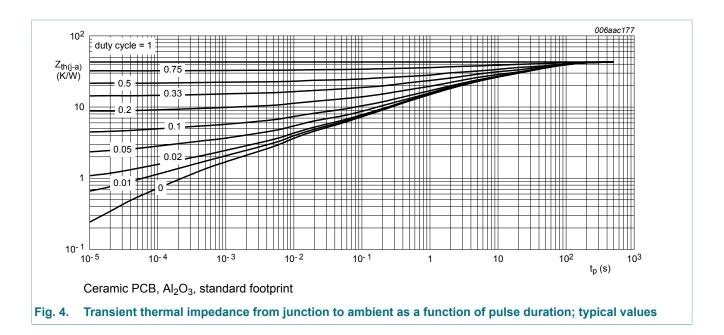


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, 7 A NPN low VCEsat (BISS) transistor

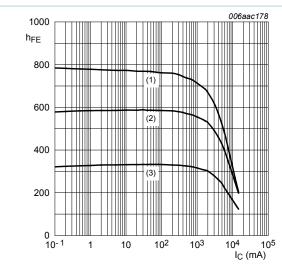


10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 16 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	300	550	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	300	550	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	300	500	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	250	450	-	
		V_{CE} = 2 V; I_{C} = 8 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	100	200	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	25	38	mV
		I_{C} = 1 A; I_{B} = 10 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \overline{o} \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	35	60	mV

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I_{C} = 2 A; I_{B} = 40 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	48	75	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	78	120	mV
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	85	140	mV
		I_C = 7 A; I_B = 350 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	137	210	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 5 A; I_{B} = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	19	28	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.82	0.9	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.92	1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.74	0.85	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	40	-	ns
t _r	rise time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	40	-	ns
t _{on}	turn-on time		-	80	-	ns
t _s	storage time		-	650	-	ns
t _f	fall time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 0.05 A;	-	75	-	ns
t _{off}	turn-off time	I _{Boff} = -0.05 A; T _{amb} = 25 °C	-	725	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	115	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	85	-	pF



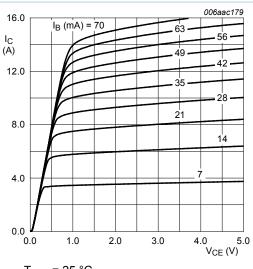
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

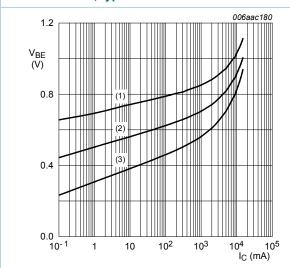
$$(3) T_{amb} = -55 °C$$

Fig. 5. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 6. Collector current as a function of collectoremitter voltage; typical values



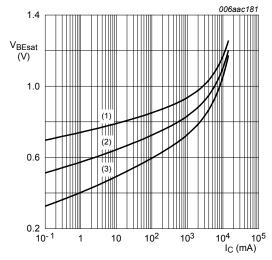
$$V_{CE} = 2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = 100 °C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



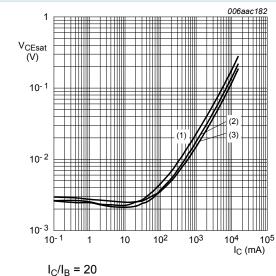
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

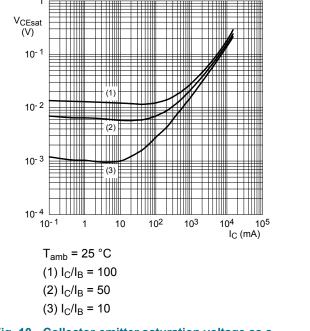
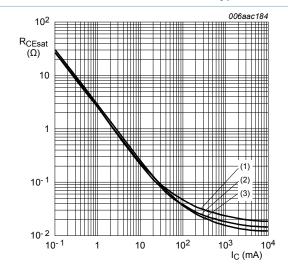


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



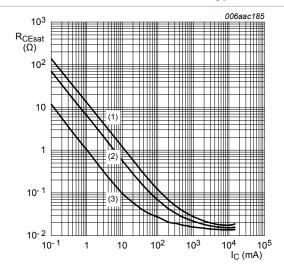
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

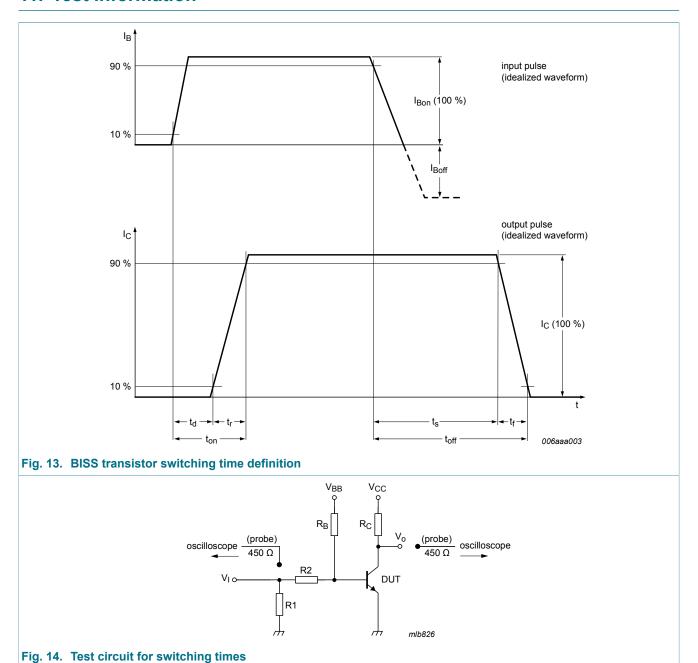
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

20 V, 7 A NPN low VCEsat (BISS) transistor

11. Test information

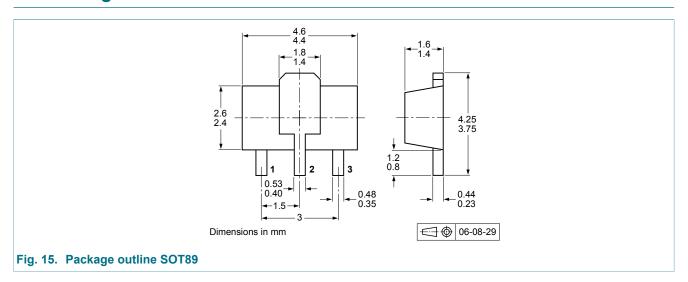


11.1 Quality information

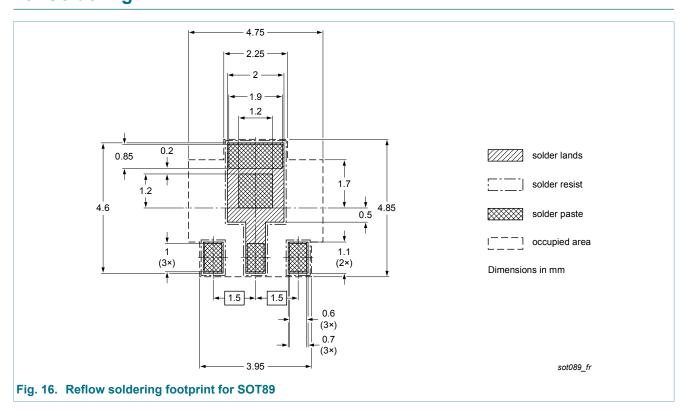
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

20 V, 7 A NPN low VCEsat (BISS) transistor

12. Package outline

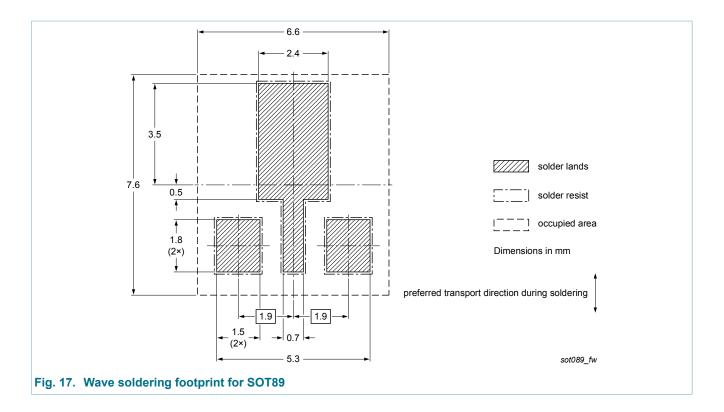


13. Soldering



10/14

20 V, 7 A NPN low VCEsat (BISS) transistor



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021NX v.3	20121211	Product data sheet	-	PBSS4021NX v.2
Modifications:	Editorial update			,
PBSS4021NX v.2	20121009	Product data sheet	-	PBSS4021NX v.1
PBSS4021NX v.1	20100401	Product data sheet	-	-

20 V, 7 A NPN low VCEsat (BISS) transistor

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15.1 Data sheet status

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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20 V, 7 A NPN low VCEsat (BISS) transistor

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20 V, 7 A NPN low VCEsat (BISS) transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	3
10	Characteristics	5
11	Test information	9
11.1	Quality information	
12	Package outline	10
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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